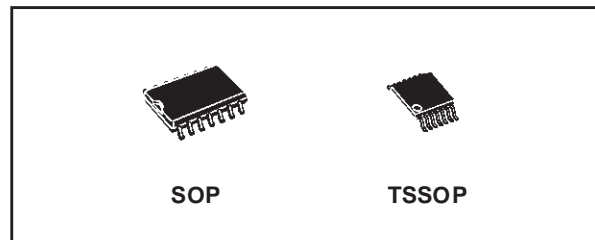




74LVX32

LOW VOLTAGE CMOS QUAD 2-INPUT OR GATE WITH 5V TOLERANT INPUTS

- HIGH SPEED :
 $t_{PD} = 4.4ns$ (TYP.) at $V_{CC} = 3.3V$
- 5V TOLERANT INPUTS
- INPUT VOLTAGE LEVEL :
 $V_{IL}=0.8V, V_{IH}=2V$ AT $V_{CC}=3V$
- LOW POWER DISSIPATION:
 $I_{CC} = 2 \mu A$ (MAX.) at $T_A=25^\circ C$
- LOW NOISE:
 $V_{OLP} = 0.3V$ (TYP.) at $V_{CC} = 3.3V$
- SYMMETRICAL OUTPUT IMPEDANCE:
 $|I_{OH}| = I_{OL} = 4mA$ (MIN)
- BALANCED PROPAGATION DELAYS:
 $t_{PLH} \cong t_{PHL}$
- OPERATING VOLTAGE RANGE:
 $V_{CC}(OPR) = 2V$ to $3.6V$ (1.2V Data Retention)
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 32
- IMPROVED LATCH-UP IMMUNITY
- POWER DOWN PROTECTION ON INPUTS



ORDER CODES

PACKAGE	TUBE	T & R
SOP	74LVX32M	74LVX32MTR
TSSOP		74LVX32TTR

The internal circuit is composed of 2 stages including buffer output, which provides high noise immunity and stable output.

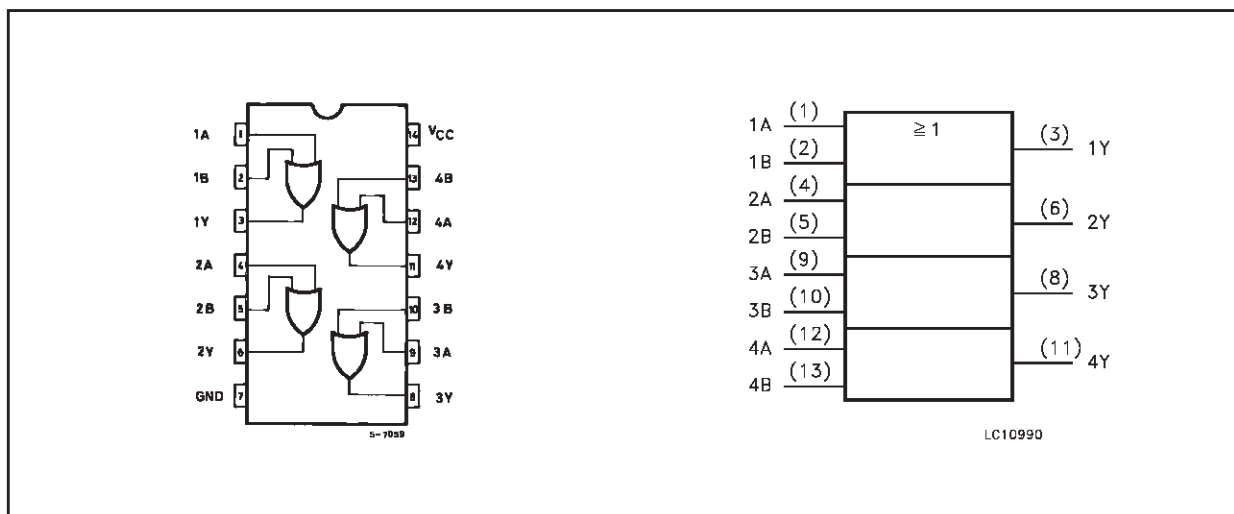
Power down protection is provided on all inputs and 0 to 7V can be accepted on inputs with no regard to the supply voltage.

This device can be used to interface 5V to 3V system. It combines high speed performance with the true CMOS low power consumption. All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.

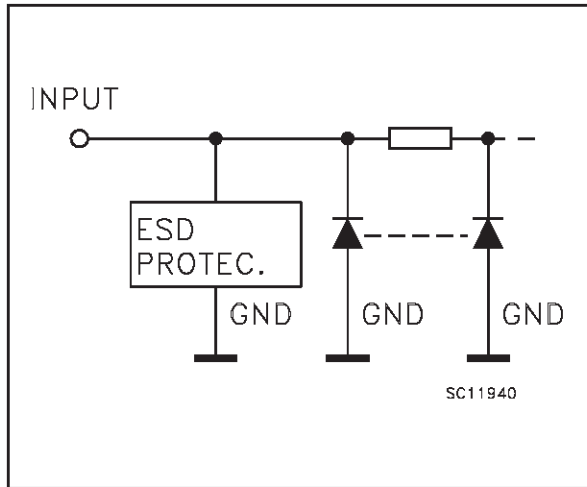
DESCRIPTION

The 74LVX32 is a low voltage CMOS QUAD 2-INPUT OR GATE fabricated with sub-micron silicon gate and double-layer metal wiring C²MOS technology. It is ideal for low power, battery operated and low noise 3.3V applications.

PIN CONNECTION AND IEC LOGIC SYMBOLS



INPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 4, 9, 12	1A to 4A	Data Inputs
2, 5, 10, 13	1B to 4B	Data Inputs
3, 6, 8, 11	1Y to 4Y	Data Outputs
7	GND	Ground (0V)
14	V _{CC}	Positive Supply Voltage

TRUTH TABLE

A	B	Y
L	L	L
L	H	H
H	L	H
H	H	H

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7.0	V
V _I	DC Input Voltage	-0.5 to +7.0	V
V _O	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	- 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
I _O	DC Output Current	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage (note 1)	2 to 3.6	V
V _I	Input Voltage	0 to 5.5	V
V _O	Output Voltage	0 to V _{CC}	V
T _{op}	Operating Temperature	-55 to 125	°C
dt/dv	Input Rise and Fall Time (note 2) (V _{CC} = 3.3V)	0 to 100	ns/V

1) Truth Table guaranteed: 1.2V to 3.6V

2) V_{IN} from 0.8V to 2.0V

DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V _{IH}	High Level Input Voltage	2.0		1.5			1.5		1.5		V
		3.0		2.0			2.0		2.0		
		3.6		2.4			2.4		2.4		
V _{IL}	Low Level Input Voltage	2.0				0.5		0.5		0.5	V
		3.0				0.8		0.8		0.8	
		3.6				0.8		0.8		0.8	
V _{OH}	High Level Output Voltage	2.0	I _O =-50 μA	1.9	2.0		1.9		1.9		V
		3.0	I _O =-50 μA	2.9	3.0		2.9		2.9		
		3.0	I _O =-4 mA	2.58			2.48		2.4		
V _{OL}	Low Level Output Voltage	2.0	I _O =50 μA		0.0	0.1		0.1		0.1	V
		3.0	I _O =50 μA		0.0	0.1		0.1		0.1	
		3.0	I _O =4 mA			0.36		0.44		0.55	
I _I	Input Leakage Current	3.6	V _I = 5V or GND			± 0.1		± 1		± 1	μA
I _{CC}	Quiescent Supply Current	3.6	V _I = V _{CC} or GND			2		20		20	μA

DYNAMIC SWITCHING CHARACTERISTICS

Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V _{OLP}	Dynamic Low Voltage Quiet	3.3	C _L = 50 pF		0.3	0.5					V
V _{OLV}	Output (note 1, 2)			-0.5	-0.3						
V _{IHD}	Dynamic High Voltage Input (note 1, 3)			2							
V _{ILD}	Dynamic Low Voltage Input (note 1, 3)					0.8					

1) Worst case package.

2) Max number of outputs defined as (n). Data inputs are driven 0V to 3.3V, (n-1) outputs switching and one output at GND.

3) Max number of data inputs (n) switching. (n-1) switching 0V to 3.3V. Inputs under test switching: 3.3V to threshold (V_{ILD}), 0V to threshold (V_{IHD}), f=1MHz.

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3\text{ns}$)

Symbol	Parameter	Test Condition		Value						Unit	
		V_{CC} (V)	C_L (pF)	$T_A = 25^\circ\text{C}$			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
t_{PLH} t_{PHL}	Propagation Delay Time	2.7	15		5.8	10.7	1.0	13.5	1.0	14.5	ns
		2.7	50		8.3	14.2	1.0	17.0	1.0	18.0	
		3.3 ^(*)	15		4.4	6.6	1.0	8.0	1.0	9.5	
		3.3 ^(*)	50		6.9	10.1	1.0	11.5	1.0	12.5	
t_{OSLH} t_{OSHL}	Output To Output Skew Time (note 1, 2)	2.7	50		0.5	1.0		1.5		1.5	ns
		3.3 ^(*)	50		0.5	1.0		1.5		1.5	

1) Skew is defined as the absolute value of the difference between the actual propagation delay for any two outputs of the same device switching in the same direction, either HIGH or LOW

2) Parameter guaranteed by design

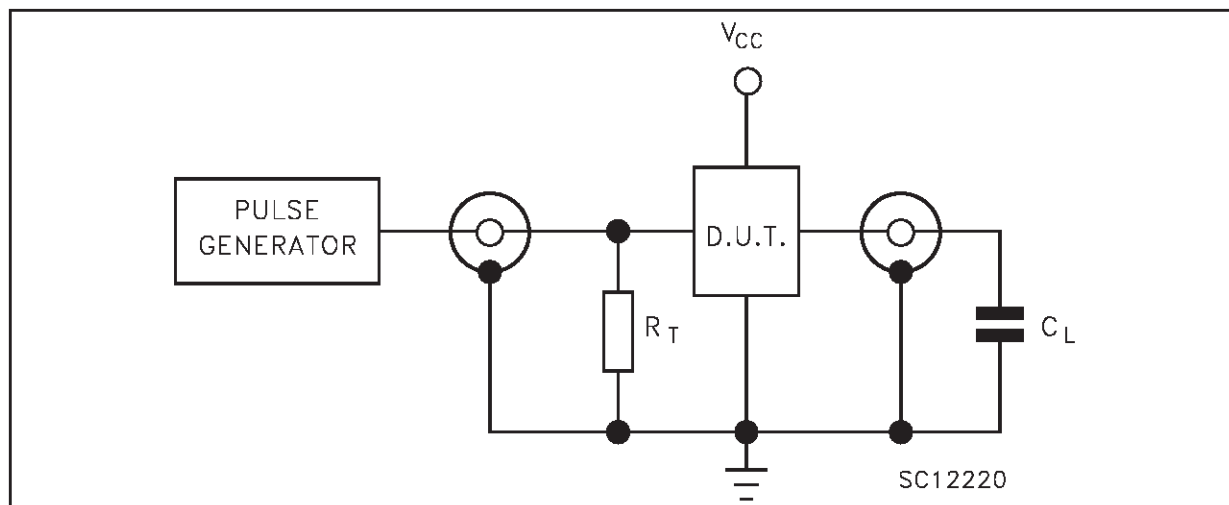
(*) Voltage range is $3.3\text{V} \pm 0.3\text{V}$

CAPACITIVE CHARACTERISTICS

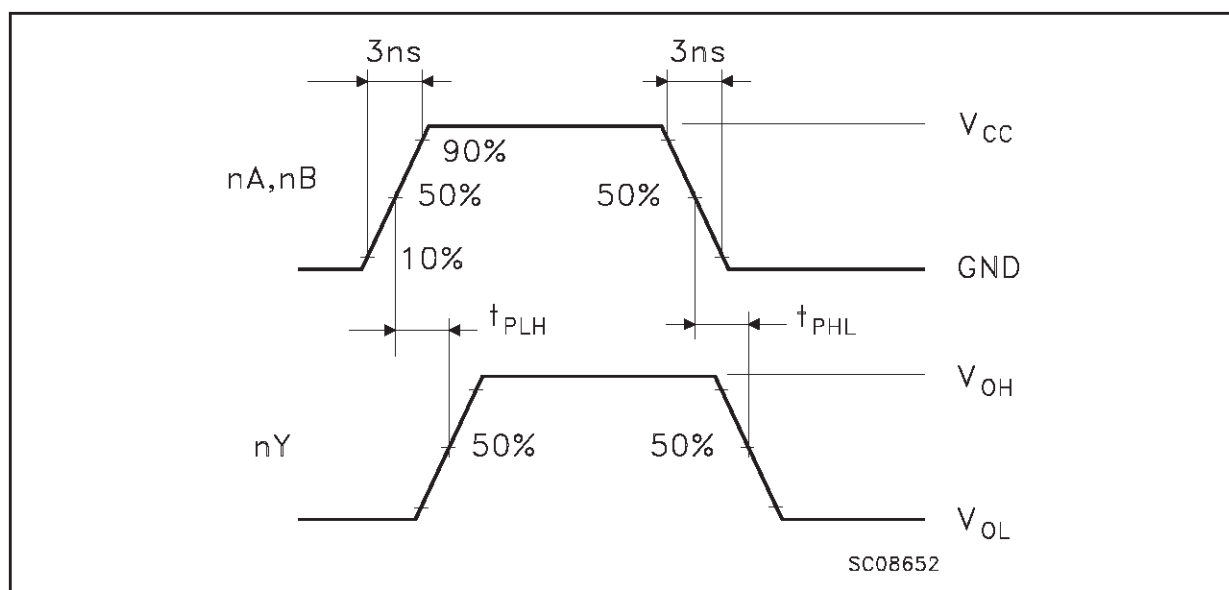
Symbol	Parameter	Test Condition		Value						Unit	
		V_{CC} (V)		$T_A = 25^\circ\text{C}$			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
C_{IN}	Input Capacitance	3.3			4	10		10		10	pF
C_{PD}	Power Dissipation Capacitance (note 1)	3.3			14						pF

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(oper)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/4$ (per gate)

TEST CIRCUIT

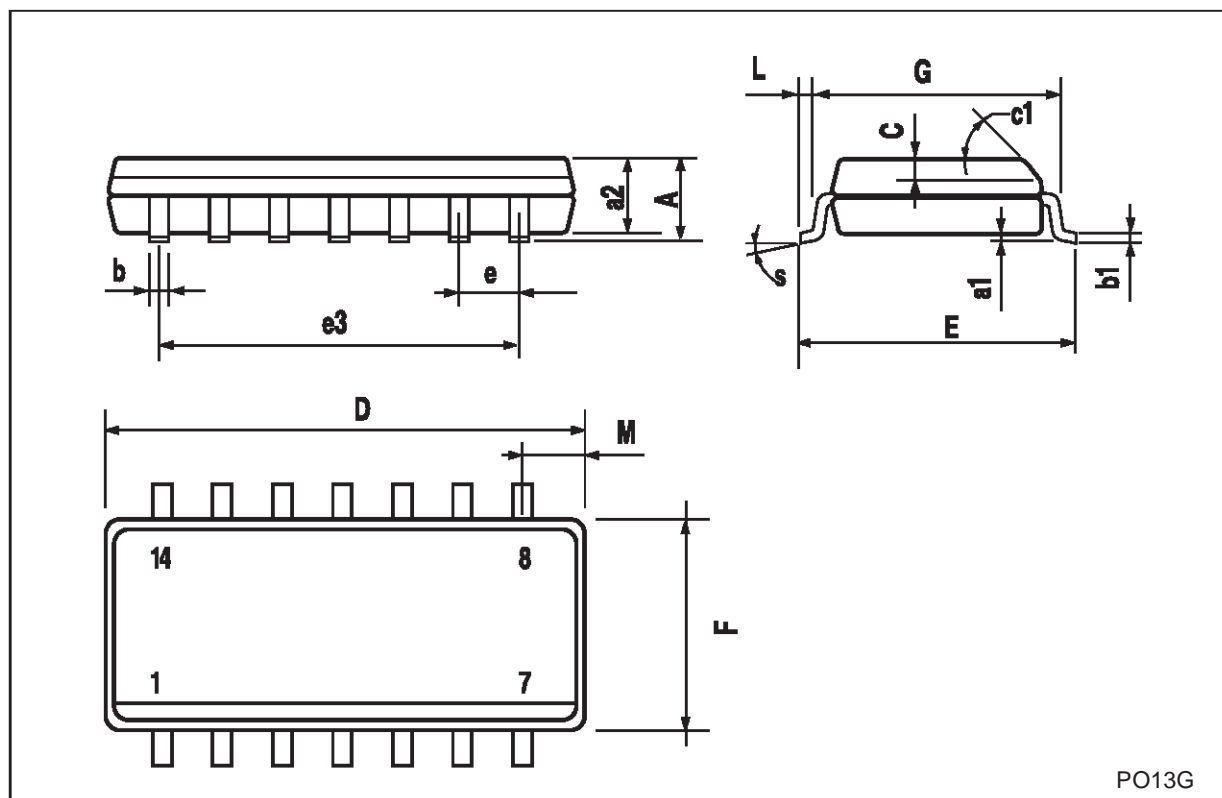


$C_L = 15/50\text{pF}$ or equivalent (includes jig and probe capacitance)
 $R_T = Z_{OUT}$ of pulse generator (typically 50Ω)

WAVEFORM : PROPAGATION DELAYS ($f=1\text{MHz}$; 50% duty cycle)

SO-14 MECHANICAL DATA

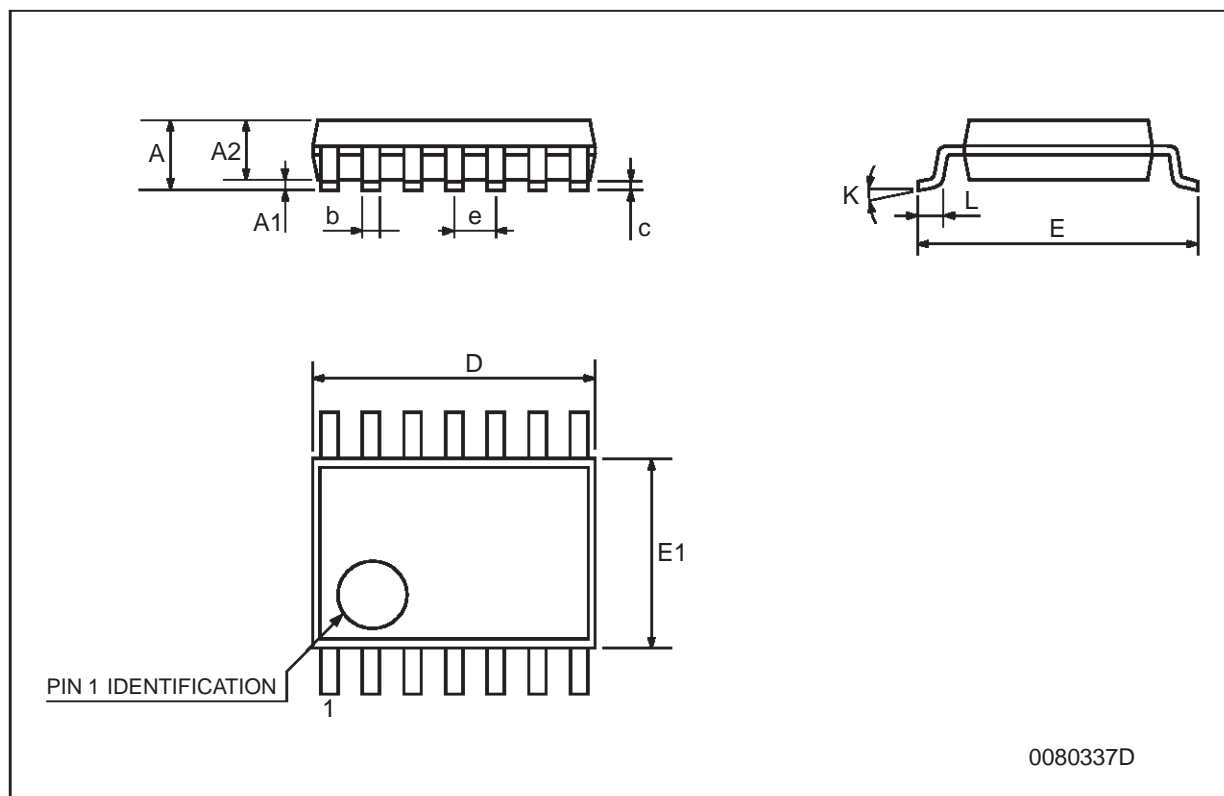
DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8° (max.)					



PO13G

TSSOP14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.0089
D	4.9	5	5.1	0.193	0.197	0.201
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



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